L Number	Hits	Search Text	DB	Time stamp
-	2	("20020042201").PN.	USPAT;	2003/04/28 09:42
' '	I	1	US-PGPUB;	
-1 .	ı		EPO; JPO; DERWENT;	
1 1	1		IBM TDB	
- 1	3156		USPAT;	2003/04/29 07:54
		or nitride or oxynitride or siN or sion)	US-PGPUB;	
ĺ			EPO; JPO;	
			DERWENT; IBM TDB	
-	599		USPAT;	2003/04/28 09:45
		or nitride or oxynitride or siN or sion)	US-PGPUB;	
!			EPO; JPO;	
1			DERWENT; IBM TDB	1
-	100	bpsg with cmp with (darc or hard adj oxide	USPAT;	2003/04/28 10:08
		or nitride or oxynitride or siN or sion)	US-PGPUB;	2000,01,20 20,00
			EPO; JPO;	
			DERWENT;	
_	113	(metal or conductive or electrode or	IBM_TDB USPAT;	2003/04/28 10:09
	110	tungsten or polysilicon) with bpsg same	US-PGPUB;	2003/04/26 10:09
		cmp same (darc or hard adj oxide or	EPO; JPO;	
1		nitride or oxynitride or siN or sion)	DERWENT;	1
i	42	(metal or conductive or electrode or	IBM_TDB	2002/04/20 10 10
	42	tungsten or polysilicon) with bpsg with	USPAT; US-PGPUB;	2003/04/28 10:19
1		cmp with (darc or hard adj oxide or	EPO; JPO;	
1	The state of the s	nitride or oxynitride or siN or sion)	DERWENT;	
	21.00	(420/070 050 600 600 760 #600#) 0070	IBM_TDB	
-	2160	(438/970,959, 692, 693, 760, "698").CCLS.	USPAT;	2003/04/29 07:54
			US-PGPUB; EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	0	("(cmp or polishing) and 7").PN.	USPAT;	2003/04/28 10:22
			US-PGPUB; EPO; JPO;	
i i			DERWENT;	
			IBM TDB	
! - !	1787	(cmp or polishing) and ((438/970,959, 692,	USPAT;	2003/04/28 10:31
		693, 760, "698").CCLS.)	US-PGPUB; EPO; JPO;	
			DERWENT;	
		·	IBM TDB	
-	288	((cmp or polishing) and ((438/970,959,	USPĀT;	2003/04/28 10:25
		692, 693, 760, "698").CCLS.)) and (bpsg and (darc or hard adj oxide or nitride or	US-PGPUB;	
		oxynitride or siN or sion))	EPO; JPO; DERWENT;	
i		- 1 Jan 1 Ja	IBM TDB	
1 -		(((cmp or polishing) and ((438/970,959,	USPAT;	2003/04/28 10:31
1		692, 693, 760, "698").CCLS.)) and (bpsg	US-PGPUB;	
1 .	1	and (darc or hard adj oxide or nitride or oxynitride or siN or sion))) not ((metal	EPO; JPO; DERWENT;	
		or conductive or electrode or tungsten or	IBM TDB	
		polysilicon) with bpsg with cmp with (darc	_ 1	
		or hard adj oxide or nitride or oxynitride		
	290	or siN or sion)) (438/754).CCLS.	USPAT;	2003/04/20 10.21
	250	(155), 54).0015.	US-PGPUB;	2003/04/28 10:31
	-		EPO; JPO;	
			DERWENT;	
ļ_	290	((438/754) CCIS \ (/cmp or poliching)	IBM_TDB	2002/04/20 10:20
i	290	((438/754).CCLS.) ((cmp or polishing) and ((438/754).CCLS.))	USPAT; US-PGPUB;	2003/04/28 10:32
	İ		EPO; JPO;	
			DERWENT;	
	<u>j</u>		IBM_TDB	

	0.54			
-	364	((((cmp or polishing) and ((438/970,959,	USPAT;	2003/04/28 10:32
		692, 693, 760, "698").CCLS.)) and (bpsg	US-PGPUB;	
1		and (darc or hard adj oxide or nitride or	EPO; JPO;	
	1	oxynitride or siN or sion))) not ((metal	DERWENT;	
		or conductive or electrode or tungsten or	IBM_TDB	
		polysilicon) with bpsg with cmp with (darc		
		or hard adj oxide or nitride or oxynitride		
	ſ	or siN or sion))) ((cmp or polishing) and		
		((438/754).CCLS.))		
-	95	(cmp or polishing) and ((438/754).CCLS.)	USPAT;	2003/04/28 10:32
	1		US-PGPUB;	
1	1		EPO; JPO;	4
1	1		DERWENT;	
İ	1		IBM_TDB	
-	8923	bpsg and (darc or hard adj oxide or	USPĀT;	2003/04/29 07:54
		nitride or oxynitride or siN or sion)	US-PGPUB;	
	1		EPO; JPO;	
1	1		DERWENT;	
			IBM TDB	
-	2167	(438/970,959,692,693,760,698).CCLS.	USPAT;	2003/04/29 07:58
			US-PGPUB;	
			EPO; JPO;	
Î	ŧ		DERWENT;	
			IBM TDB	
j -	2935	(438/970,959,692,693,760,698,745,754).CCLS.	USPAT;	2003/04/29 08:00
			US-PGPUB;	
			EPO; JPO;	
		*	DERWENT;	
!			IBM TDB	
-	1961	((438/970,959,692,693,760,698,745,754).CCLS	. USPĀT;	2003/04/29 08:00
J	!	and (cmp or polishing)	US-PGPUB;	
	÷ i		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	317	(((438/970,959,692,693,760,698,745,754).CCL		2003/04/29 09:25
		and (cmp or polishing)) and (bpsg and	US-PGPUB;	
		(darc or hard adj oxide or nitride or	EPO; JPO;	
		oxynitride or siN or sion))	DERWENT;	
!	1		IBM TDB	
<b>!</b> —	553	(low adj "k" adj dielectric) same (darc or	USPAT;	2003/04/29 09:28
!	i !	nitride or sion)	US-PGPUB;	
-	!		EPO; JPO;	
!			DERWENT;	
	1		IBM TDB	